

IN THE CLAIMS:

Kindly amend Claim 1 as follows:

Subt B'

1. (Amended) A lateral metal-oxide semiconductor field effect transistor (MOSFET), comprising:

A³
 a silicon carbide layer located on or within a substrate of a semiconductor wafer, a gate formed on the silicon carbide layer; and

source and drain regions located in the silicon carbide layer and laterally offset from the gate.
